

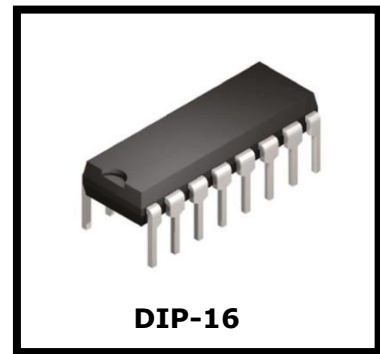
Bipolar Stepping Motor Driver IC

Description

The AP8100 is 2 phase stepping motor driver IC. It consists of TTL compatible input circuits, dual bridge driver outputs with flyback diodes, changing circuit of motor coil drive voltage (Power saving circuit) and stand-by circuit

Features

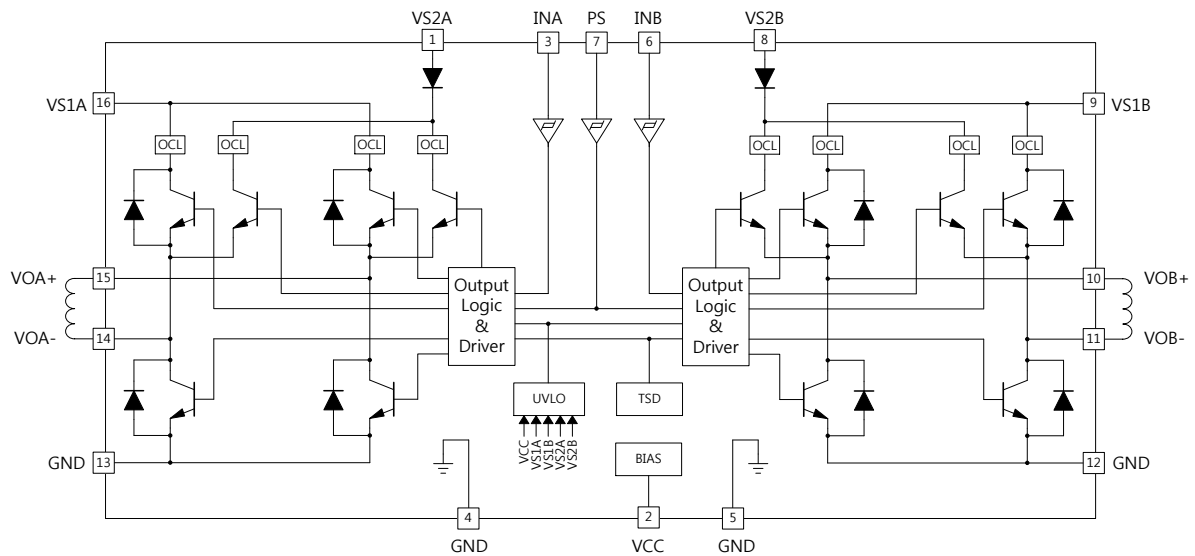
- One Chip 2 Phase Stepping Motor Driver including two bridge drivers
- Power Saving and Stand-by Operation
- Short-Through Current Restriction Circuit
- TTL Compatible Inputs
- Output Current up to 400mA(Peak)
- Over Current Shutdown Circuit
- Thermal Shutdown Circuit
- Under Voltage Lockout Circuit
- Pull-down Resistance for Input



Application

- FDD, Refrigerator Actuator

Block Diagram



Note : Pin 4, 5, 12 and 13 are internally connected.

Pin Description

Pin No	Symbol	Functional Description
1	VS2A	Low-voltage power supply terminal
2	VCC	Power voltage supply terminal for control
3	INA	A-ch forward rotation / reverse rotation signal input terminal, Truth Table 1
6	INB	B-ch forward rotation / reverse rotation signal input terminal, Truth Table 1
7	PS	Power saving signal input terminal
8	VS2B	Standby signal input terminal, Truth Table 2
9	VS1B	High-voltage power supply terminal
10	VOB+	Output B+
11	VOB-	Output B-
14	VOA-	Output A-
15	VOA+	Output A+
16	VS1A	High-voltage power supply terminal
4, 5, 12, 13	GND	GND terminal (Logic and Power GND)

Truth Table 1.

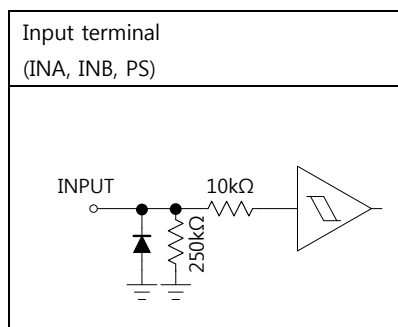
Input		Output (x : A, B)		
PS	IN	VOx+	VOx-	Mode
L	L	L	H	ENABLE V _{S1}
L	H	H	L	ENABLE V _{S1}
H	L	L	H	ENABLE V _{S2} (Power saving)
H	H	H	L	ENABLE V _{S2} (Power saving)

Truth Table 2.

VS2B	Mode
L	POWER OFF (Standby mode)
H	OPERATION

Note : Apply 5V to VS2A as a supply terminal.

Terminal Circuit



The diagram is partly-provided and omitted or simplified for explanatory purposes.



Maximum Ratings Characteristics

(T_A = 25°C unless otherwise specified)

Characteristics	Symbol	Value	Unit
Supply voltage	V _{CC}	7.0	V
	V _{S1}	17.0	
	V _{S2}	V _{CC}	
Output current	I _O (PEAK)	±400	mA
	I _O (START)	±350	
	I _O (HOLD)	±100	
Input voltage	V _{IN}	V _{CC}	V
Power dissipation	P _D	1.4	W
Operating temperature	T _{opr}	-30 ~ 75	°C
Storage temperature	T _{stg}	-55 ~ 150	°C

Recommended Operating Conditions

(T_A = 25°C unless otherwise specified)

Characteristics	Symbol	Min	Typ.	Max	Unit
Supply voltage	V _{CC}	4.5	-	5.5	V
	V _{S1}	-	12	-	
	V _{S2}	2.7	-	5.5	
	V _{IN}	-	-	V _{CC}	

* Operating Voltage Restriction : V_{S1} ≥ V_{S2A}



Electrical Characteristics

($T_A = 25^{\circ}\text{C}$, $V_{CC} = 5\text{V}$, $V_{S1} = 12\text{V}$, $V_{S2A} = 5\text{V}$ unless otherwise specified)

Characteristics	Symbol	Test Circuit	Condition	Min	Typ.	Max	Unit
UNDER VOLTAGE LOCKOUT SECTION							
Start Threshold Voltage	V _{ST}	-	V _{CC} Increasing	3.7	4.21	4.5	V
UVLO Hysteresis	V _{HYS}	-	-	-	0.1	-	V
SUPPLY CURRENT SECTION							
V _{CC} Supply Current	ICC1	1	PS : H, VS2 : H	-	3.1	4.5	mA
	ICC2		PS : L, VS2 : H	-	3.1	4.5	
	ICC3		PS : L, VS2 : L	-	65	100	μA
VS1 Supply Current	IVS1	1	PS : L	-	1.6	3	mA
VS2 Supply Current	IVS2	1	PS : L	-	1.6	2.4	
	IVS2_ON	1	PS : H	-	2.5	3.75	
INPUT VOLTAGE SECTION							
Input Logic High Level	V _{INH}	-	VS2 : H	2.0	-	V _{CC}	V
Input Logic Low Level	V _{INL}	-		0	-	0.8	
PS Input High Level	V _{PSH}	-		2.0	-	V _{CC}	
PS Input Low Level	V _{PSL}	-		0	-	0.8	
INPUT CURRENT SECTION							
Logic Input Current	I _{IN}	-	V _{IN/PS} = 5V	-	20	30	μA
PS Input Current	I _{PS}	-					
OUTPUT VOLTAGE SECTION							
Output Saturation Voltage	V _{SAT1H1}	3	PS : L, VS2 : H, I _{OUT} = 100mA	-	1.14	-	V
	V _{SAT1H2}	3	PS : L, VS2 : H, I _{OUT} = 400mA	-	1.39	-	
	V _{SAT2H1}	3	PS : H, VS2 : H, I _{OUT} = 30mA	-	1.94	-	
	V _{SAT2H2}	3	PS : H, VS2 : H, I _{OUT} = 100mA	-	2.19	-	
	V _{SATL1}	3	VS2 : H, I _{OUT} = 30mA	-	0.14	-	
	V _{SATL2}	3	VS2 : H, I _{OUT} = 100mA	-	0.24	-	
	V _{SATL3}	3	VS2 : H, I _{OUT} = 400mA	-	0.59	-	
DIODE SECTION							
Diode Forward Voltage	V _{FU1}	2	I _F = 30mA	-	0.91	-	V
	V _{FD1}	2		-	0.76	-	
	V _{FU2}	2	I _F = 100mA	-	1.02	-	
	V _{FD2}	2		-	0.89	-	
	V _{FU3}	2	I _F = 350mA	-	1.30	-	
	V _{FD3}	2		-	1.21	-	
OUTPUT DELAY SECTION							
Delay Time	t _{pLH}	-	Output Rising	-	6.3	-	us
	t _{pHL}	-	Output Falling	-	0.6	-	

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Characteristics	Symbol	Test Circuit	Condition	Min	Typ.	Max	Unit
PROTECTION SECTION*							
Thermal Shutdown	TSD	-	-	-	170	-	°C
TSD Hysteresis	TSDhys	-	-	-	25	-	
Output Limit Current	I _{limit}	-	-	0.4	0.8	-	A

*: These parameters, although guaranteed, are not 100% tested in production.

Under voltage Lockout Circuit (UVLO)

An under voltage lockout circuit is included.

Outputs are turned off under the conditions as follows;

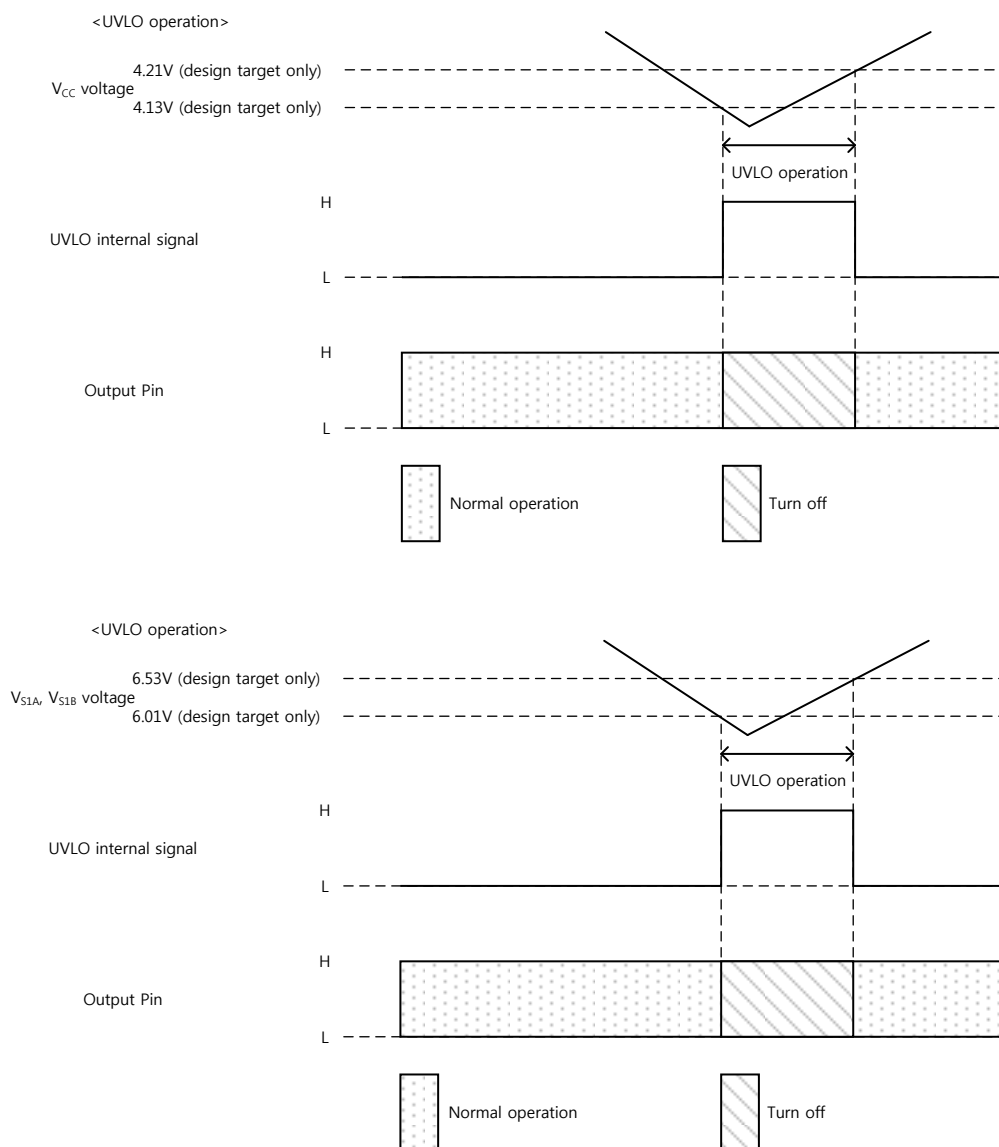
$V_{CC} \leq 4.21V$ (Design target) or

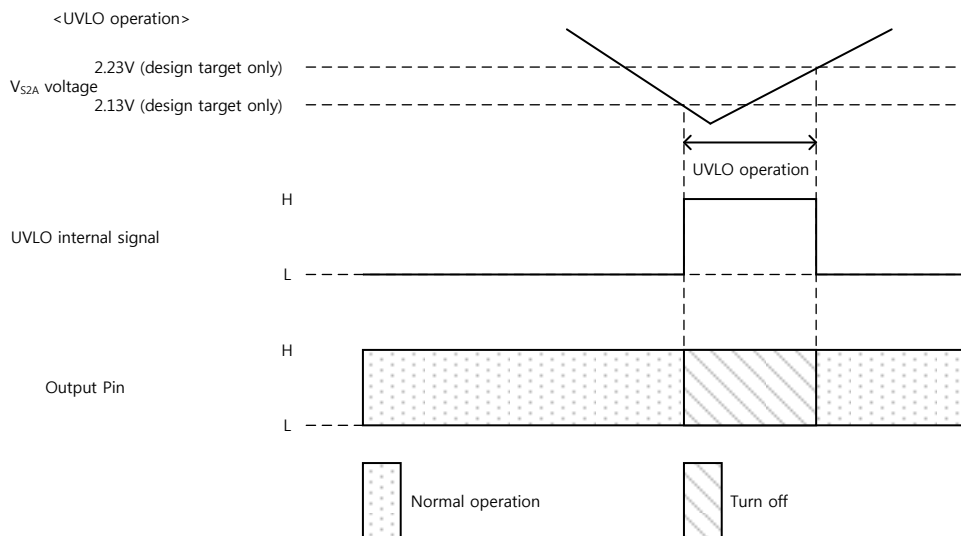
$V_{S1A} \leq 6.53V$ (Design target) and $V_{S1B} \leq 6.53V$ (Design target) or

$V_{S2A} \leq 2.23V$ (Design target)

The UVLO circuit has a hysteresis and the function recovers under the conditions as follows;

$V_{CC} = 4.21V$ (Design target), $V_{S1A}/V_{S1B} = 6.53V$ (Design target), $V_{S2A} = 2.23V$ (Design target)





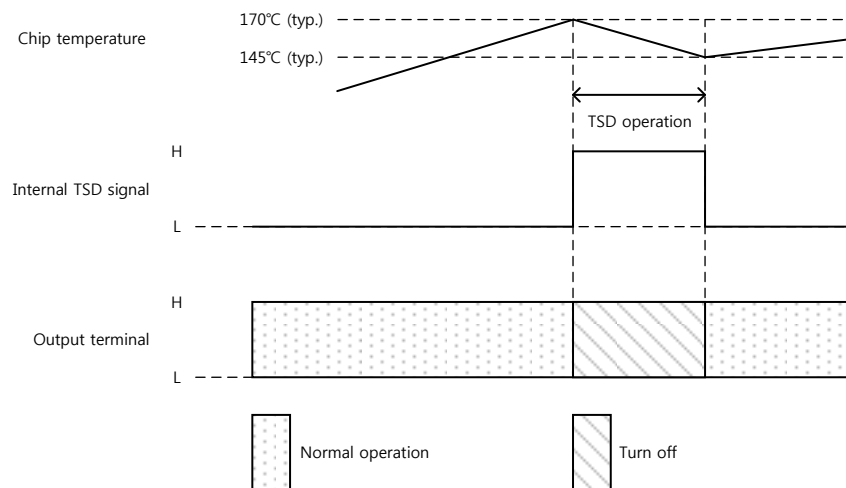
Thermal Shutdown Circuit (TSD)

The AP8100 has a thermal shutdown circuit. If the junction temperature (T_j) exceeds 170°C (design target only), all the outputs are turned off.

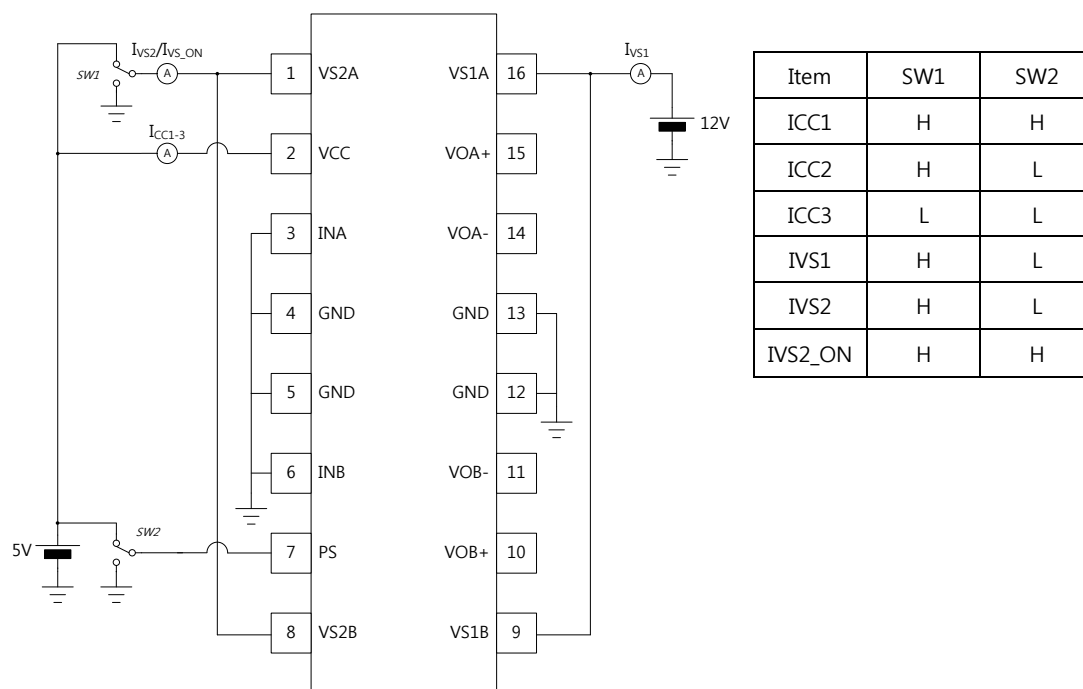
It recovers automatically at 145°C. It has a hysteresis width of 25°C.

TSD = 170°C (design target only)

<TSD operation>

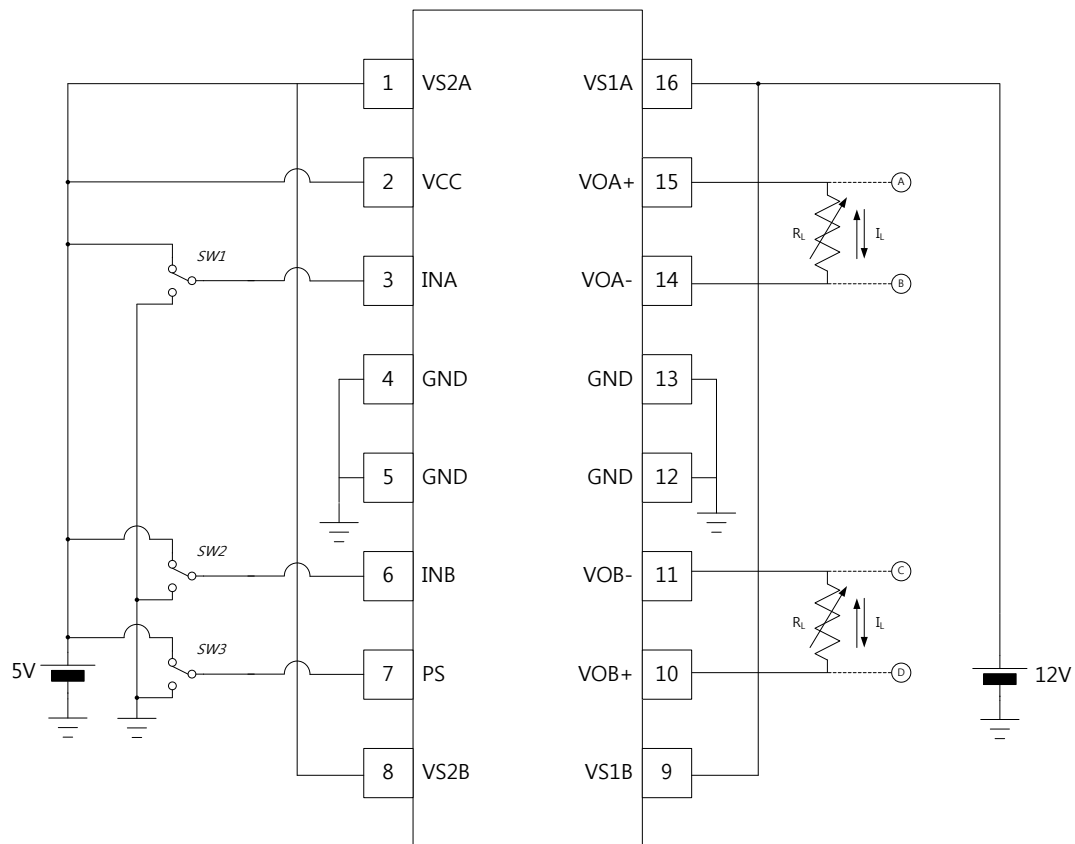


Test Circuit 1. I_{CC1} , I_{CC2} , I_{CC3} , I_{VS1} , I_{VS2} , I_{VS2_ON}



External capacitors are removed for simplified test circuit; Further information is described on "Application Circuit" below.

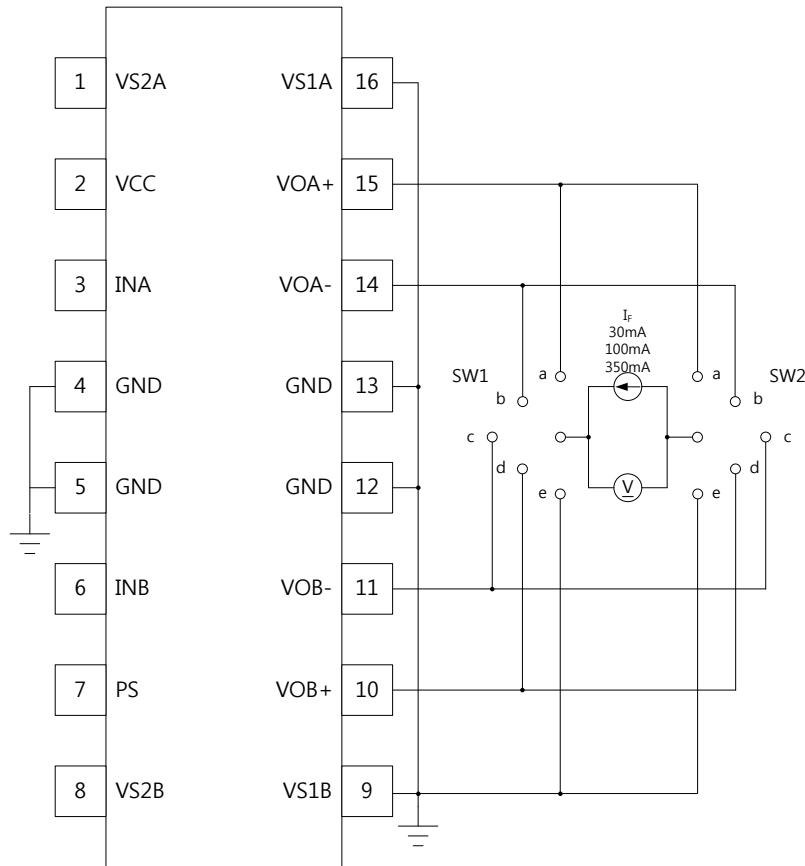
Test Circuit 2. V_{SAT1H1} , V_{SAT1H2} , V_{SAT2H1} , V_{SAT2H2} , V_{SATL1} , V_{SATL2} , V_{SATL3}



Item	IL (mA)	Output (x=A,B)	SW1	SW2	SW3	Measurement Point (A, B, C, D : node)
V_{SAT1H1}	100	VOx+	H	H	L	12V- V_{Av} 12V- V_D
		VOx-	L	L	L	12V- V_{Br} 12V- V_C
V_{SAT1H2}	400	VOx+	H	H	L	12V- V_{Av} 12V- V_D
		VOx-	L	L	L	12V- V_{Br} 12V- V_C
V_{SAT2H1}	30	VOx+	H	H	H	5V- V_{Av} 5V- V_D
		VOx-	L	L	H	5V- V_{Br} 5V- V_C
V_{SAT2H2}	100	VOx+	H	H	H	5V- V_{Av} 5V- V_D
		VOx-	L	L	H	5V- V_{Br} 5V- V_C
V_{SATL1}	30	VOx+	H	H	—	Node B, node C
		VOx-	L	L	—	Node A, node D
V_{SATL2}	100	VOx+	H	H	—	Node B, node C
		VOx-	L	L	—	Node A, node D
V_{SATL3}	400	VOx+	H	H	—	B, C
		VOx-	L	L	—	A, D

External capacitors are removed for simplified test circuit; Further information is described on "Application Circuit" below.

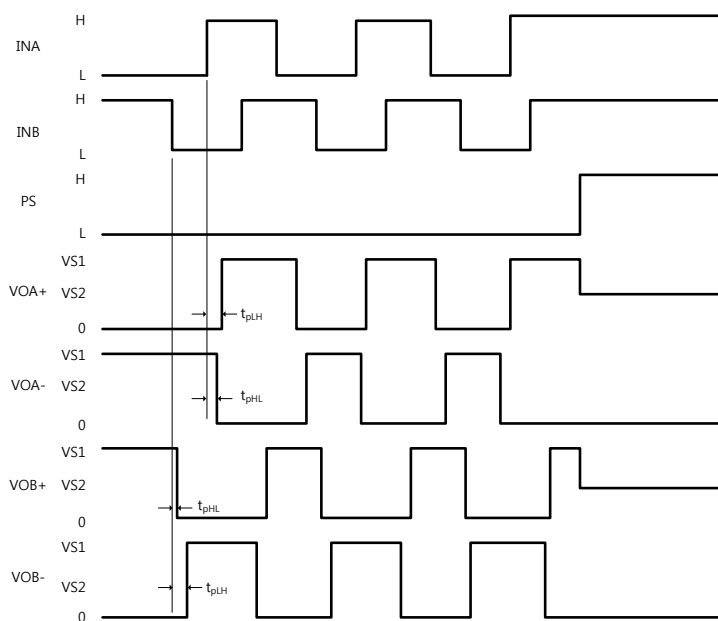
Test Circuit 3. V_{FU} , V_{FD}



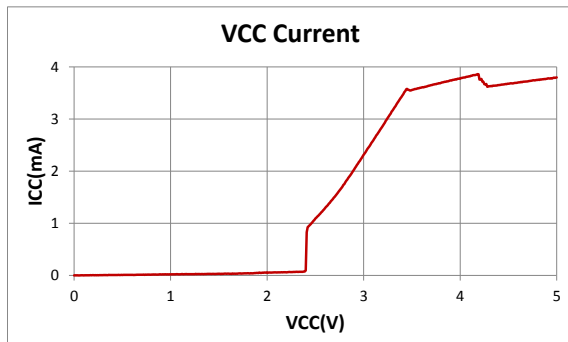
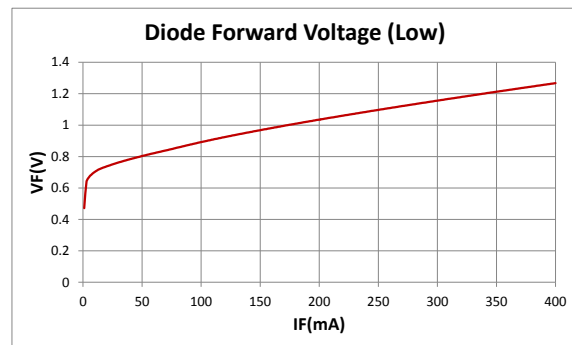
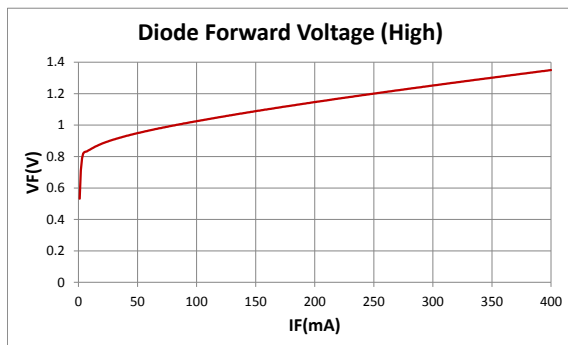
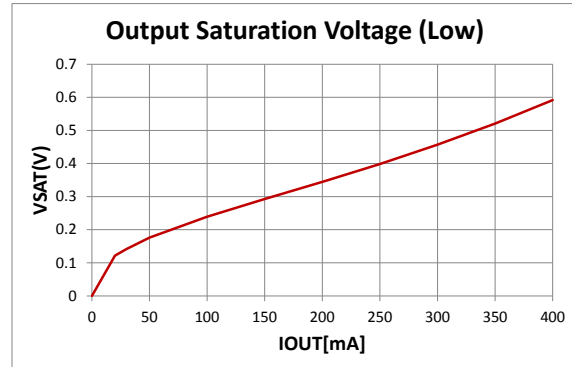
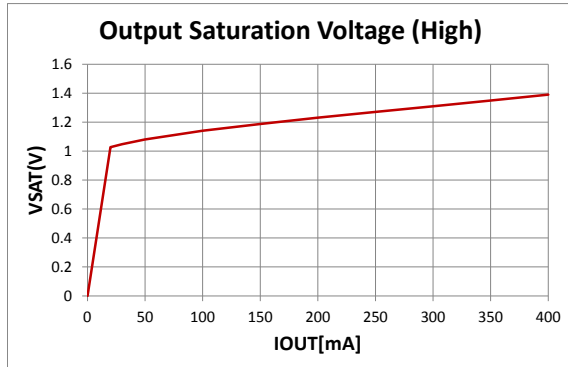
Item	SW1	SW2
VFU	a	e
	b	
	c	
	d	
VFL	e	a
		b
		c
		d

External capacitors are removed for simplified test circuit; Further information is described on "Application Circuit" below.

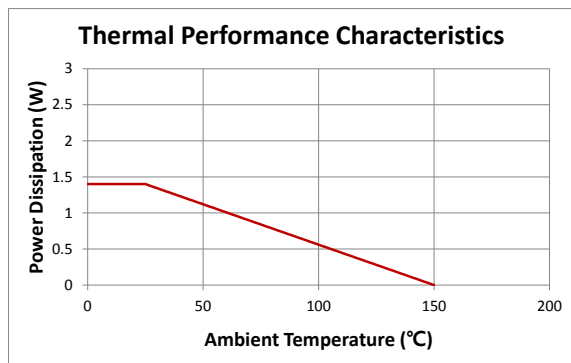
Timing Chart



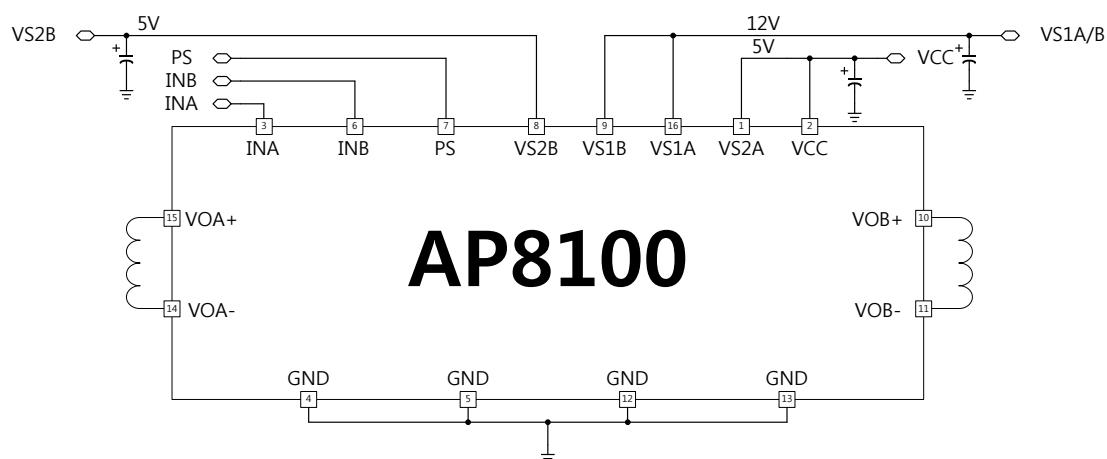
Typical Performance Characteristics



Thermal Performance Characteristics



Application Circuit

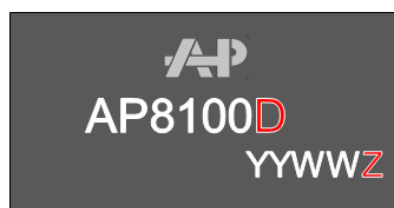




Ordering Information

Part No	Package	Packing	Finish	Halogen	Packing Unit
AP8100	DIP-16	Tube : 25pcs	Sn	Free	5,000pcs

Marking Layout



1ST Line: Company logo

2nd Line: Device name: AP8100D

-D : DIP-16 PKG code

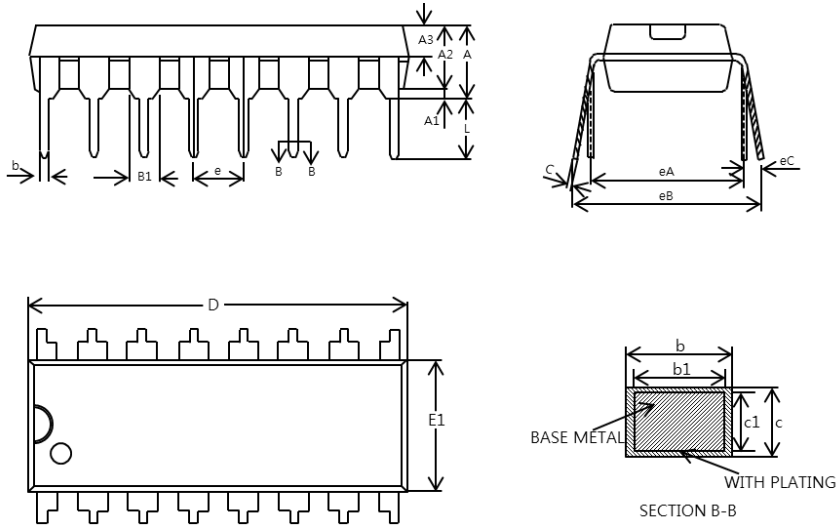
3rd Line: Date code

-YY : Last two digit of calendar year

-WW : Work week calendar

-Z : ASSEMBLY SITE

Package Dimensions



SYMBOL	MLLIMETER		
	MIN	NOM	MAX
A	3.60	3.80	4.00
A1	0.51	—	—
A2	3.20	3.30	3.40
A3	1.47	1.52	1.57
b	0.44	—	0.52
b1	0.43	0.46	0.49
B1	1.52RFE		
c	0.25	—	0.29
c1	0.24	0.25	0.26
D	19.00	19.10	19.20
E1	6.25	6.35	6.45
e	2.54BSC		
eA	7.62REF		
eB	7.62	—	9.30
eC	0	—	0.84
L	3.00	—	—

Revision History

No	Date	Contents
REV00	2017-03-28	Initial Brief Datasheet Release
REV01	2018-03-20	Start Threshold Voltage Revised

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